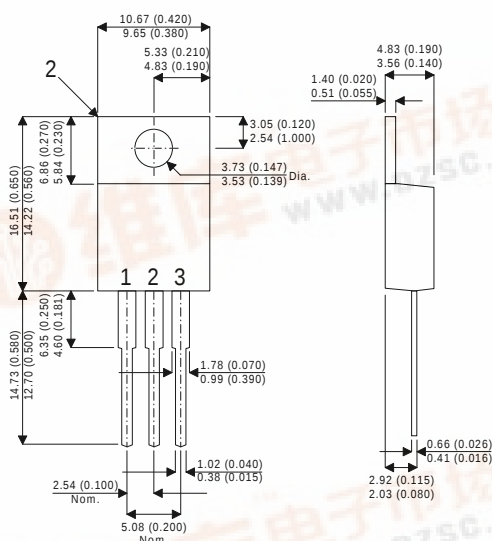


N-CHANNEL ENHANCEMENT MODE HIGH VOLTAGE ISOLATED POWER MOSFETS



V_{DSS} 1500V

 $I_{D(\text{cont})} \quad 0.1\text{A}$ $R_{DS(on)} \quad 140\Omega$

Pin 1 – Gate Pin 2 – Drain Pin 3 – Source

ABSOLUTE MAXIMUM RATINGS ($T_{AMB} = 25^{\circ}\text{C}$ unless otherwise stated)

V _{DSS}	Drain – Source Voltage	1500	V
I _D	Continuous Drain Current	0.1	A
I _{DM}	Pulsed Drain Current	0.2	A
V _{GS}	Gate – Source Voltage	±20	V
P _D	Total Power Dissipation	20	W
T _J , T _{STG}	Operating and Storage Junction Temperature Range	–55 to +150	°C

ELECTRICAL CHARACTERISTICS (T_{AMB} = 25°C unless otherwise stated)

	Characteristic	Test Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain – Source Breakdown Voltage	V _{GS} = 0V , I _D = 1mA	1500			V
R _{DS(ON)}	Drain – Source On State Resistance	V _{GS} =10V , I _D = 50mA		140	200	Ω
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 1200V , V _{GS} = 0V			100	μA
I _{GSS}	Gate – Source Leakage Current	V _{GS} = ±20V , V _{DS} = 0V			±100	nA
V _{GS(off)}	Cutoff Voltage	V _{DS} = 10V , I _D = 1.0mA	1.5		3.5	V
C _{iss}	Input Capacitance	V _{DS} = 20V f = 1MHz		40		pF
C _{oss}	Output Capacitance			12		
C _{rss}	Reverse Transfer Capacitance			3.0		
t _{on}	Turn-on Time	V _{GS} = 10V		40		ns
t _{off}	Turn-off Time	I _D = 50mA		400		
V _{SD}	Diode Forward Voltage	V _{GS} = 0 , I _S = 0.1A		1.0	1.5	V
Y _{fs}	Forward Transfer Admittance	V _{DS} = 20V , I _D = 50mA	50	100		mS